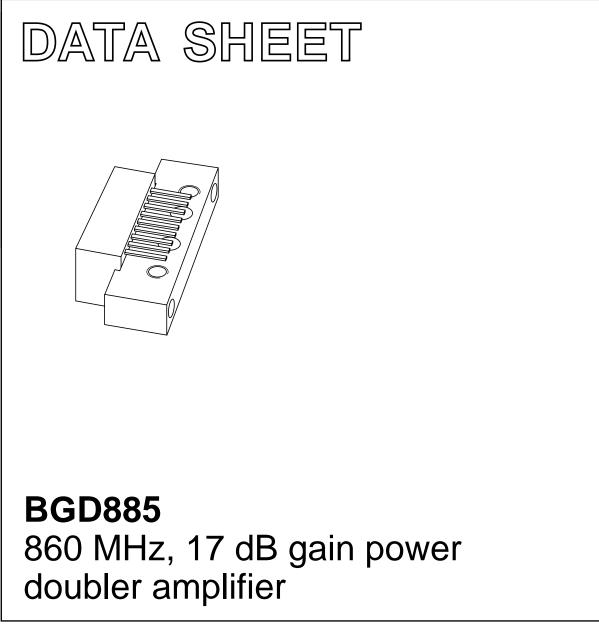
## DISCRETE SEMICONDUCTORS



Product specification Supersedes data of 2001 Oct 25 2001 Nov 02



## 860 MHz, 17 dB gain power doubler amplifier

### **BGD885**

#### FEATURES

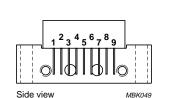
- · Excellent linearity
- · Extremely low noise
- · Silicon nitride passivation
- Rugged construction
- Gold metallization ensures excellent reliability.

#### DESCRIPTION

Hybrid amplifier module for CATV/MATV systems operating over a frequency range of 40 to 860 MHz at a voltage supply of 24 V (DC).

#### **PINNING - SOT115D**

PIN	DESCRIPTION	
1	input	
2, 3, 5, 6, 7	common	
4	10 V, 200 mA supply terminal	
8	+V <sub>B</sub>	
9	output	



Side view

Fig.1 Simplified outline.

#### QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G <sub>p</sub>	power gain	f = 50 MHz	16.5	17.5	dB
I <sub>tot</sub>	total current consumption (DC)	V <sub>B</sub> = 24 V	-	450	mA

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER		MAX.	UNIT
V <sub>B</sub>	DC supply voltage	-	26	V
Vi	RF input voltage	-	65	dBmV
T <sub>stg</sub>	storage temperature		+100	°C
T <sub>mb</sub>	operating mounting base temperature	-20	+100	°C

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#### **CHARACTERISTICS**

**Table 1** Bandwidth 40 to 860 MHz;  $V_B = 24 \text{ V}$ ;  $T_{mb} = 35 \text{ °C}$ ;  $Z_S = Z_L = 75 \Omega$ 

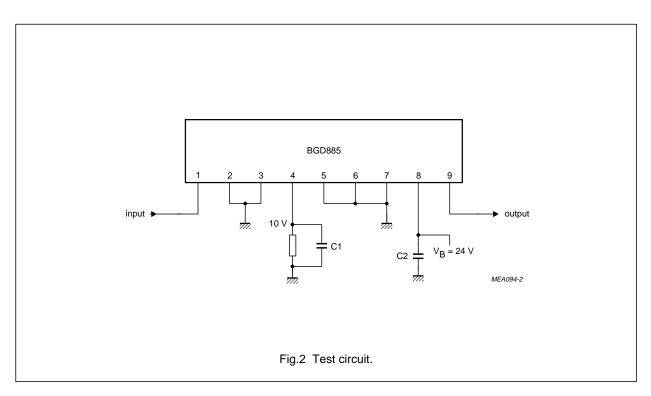
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G <sub>p</sub>	power gain	f = 50 MHz	16.5	17.5	dB
SL	slope cable equivalent	f = 40 to 860 MHz	0.2	1.6	dB
FL	flatness of frequency response	f = 40 to 860 MHz	-	±0.5	dB
S <sub>11</sub>	input return losses	f = 40 MHz; note 1	20	-	dB
		f = 800 to 860 MHz	10	-	dB
S <sub>22</sub>	output return losses	f = 40 MHz; note 1	20	-	dB
		f = 800 to 860 MHz	10	-	dB
d <sub>2</sub>	second order distortion	note 2	-	-53	dB
V <sub>o</sub> c	output voltage	d <sub>im</sub> = -60 dB; note 3	64	-	dBmV
		$d_{im} = -60 \text{ dB}; \text{ note } 4$	63	-	dBmV
F	noise figure	f = 50 MHz	-	8	dB
		f = 550 MHz	-	8	dB
		f = 650 MHz	-	8	dB
		f = 750 MHz	-	8	dB
		f = 860 MHz	-	8	dB
I <sub>tot</sub>	total current consumption (DC)	note 5	-	450	mA

#### Notes

- 1. Decrease per octave of 1.5 dB.
- 2.  $V_p = 59 \text{ dBmV}$  at  $f_p = 349.25 \text{ MHz}$ ;  $V_q = 59 \text{ dBmV}$  at  $f_q = 403.25 \text{ MHz}$ ; measured at  $f_p + f_q = 752.5 \text{ MHz}$ .
- 3. Measured according to DIN45004B:  $f_p = 341.25 \text{ MHz}; V_p = V_o;$   $f_q = 348.25 \text{ MHz}; V_q = V_o -6 \text{ dB};$   $f_r = 350.25 \text{ MHz}; V_r = V_o -6 \text{ dB};$ measured at  $f_p + f_q - f_r = 339.25 \text{ MHz}.$
- 4. Measured according to DIN45004B:  $f_p = 851.25 \text{ MHz}; V_p = V_o;$   $f_q = 858.25 \text{ MHz}; V_q = V_o -6 \text{ dB};$   $f_r = 860.25 \text{ MHz}; V_r = V_o -6 \text{ dB};$ measured at  $f_p + f_q - f_r = 849.25 \text{ MHz}.$
- 5. The module normally operates at  $V_B = 24$  V, but is able to withstand supply transients up to 30 V.

**BGD885** 

## 860 MHz, 17 dB gain power doubler amplifier



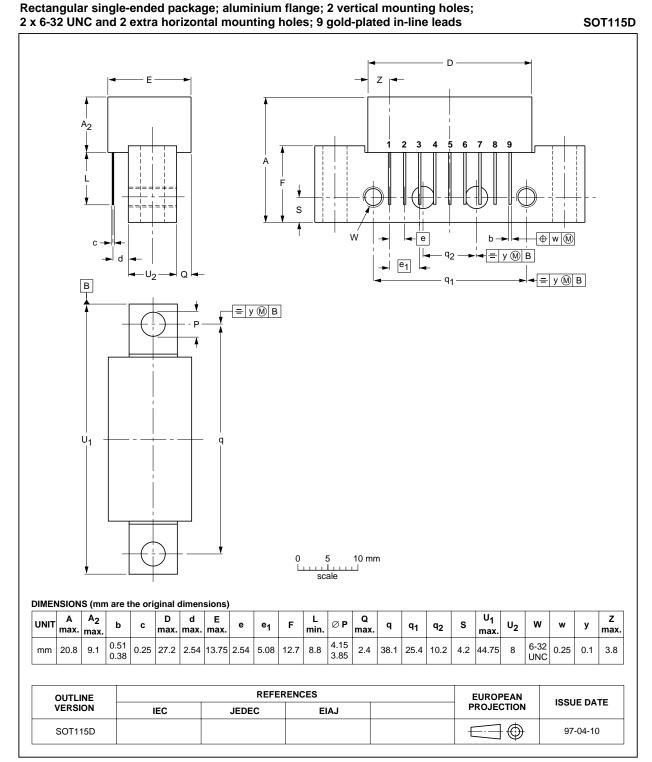
#### List of components (see Fig.2)

COMPONENT	DESCRIPTION VALUE		
C1	ceramic multilayer capacitor	1 nF (max.)	
C2	ceramic multilayer capacitor	1 nF	
R	resistor	56 Ω, 2 W	

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## 860 MHz, 17 dB gain power doubler amplifier

#### PACKAGE OUTLINE



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**BGD885** 

## 860 MHz, 17 dB gain power doubler amplifier

### **BGD885**

#### DATA SHEET STATUS

DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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NOTES

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